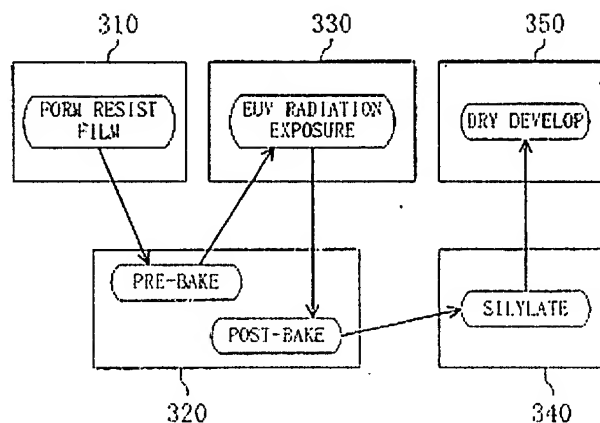


Pattern forming method and apparatus for fabricating semiconductor device**Publication number:** TW490736B**Publication date:** 2002-06-11**Inventor:** IRIE SHIGEO (JP)**Applicant:** MATSUSHITA ELECTRIC IND CO LTD (JP)**Classification:****- international:** G03F7/039; G03F7/16; G03F7/20; G03F7/26;
G03F7/36; G03F7/38; H01L21/027; G03F7/039;
G03F7/16; G03F7/20; G03F7/26; G03F7/36; G03F7/38;
H01L21/02; (IPC1-7): H01L21/027**- European:** G03F7/16Z; G03F7/26D; G03F7/38**Application number:** TW20010111446 20010514**Priority number(s):** JP20000192459 20000627**Also published as:**US6855485 (B2)
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JP2002015971 (A)[Report a data error here](#)**Abstract of TW490736B**

A resist film is formed out of a resist material on a substrate, and then pre-baked. Next, the pre-baked resist film is exposed to extreme ultraviolet radiation through a photomask. Then, the exposed resist film is developed, thereby defining a resist pattern on the substrate. The pre-baking and exposing steps are carried out in a vacuum without subjecting the resist film to the air.



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